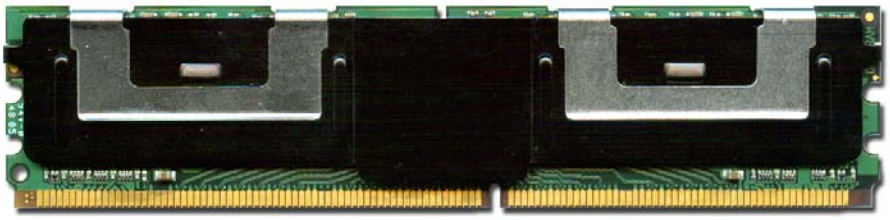
DTM65527E

2 GB – 240-Pin DDR2 Low Power FB-DIMM



Identification

DTM65527E 256Mx72
2GB 1Rx4 PC2-5300F-555-11-C1

Performance range

Clock / Module Speed / CL-t_{RCD} -t_{RP}

333MHz / DDR2-667 / 5-5-5
266MHz / DDR2-533 / 4-4-4
200MHz / DDR2-400 / 3-3-3

Features

- 240-pin JEDEC-compliant DIMM, 133.35 mm wide by 30.35 mm high
- Data Transfer Rate: 5.3 Gigabytes/sec
- Operating Voltage: VDD = 1.8 V ±0.1; VCC = 1.5V ±0.1
- SMBus interface to AMB for configuration register access
- MBIST and IBIST test functions
- Transparent mode for DDR2 SDRAM test support
- Full DIMM Heat Spreader
- High-speed differential point-to-point link
- Fully RoHS Compliant

Description

The DTM65527E is a single rank PC2-5300 Fully Buffered 256MX72 ECC DIMM that conforms to the JEDEC FB-DIMM standard. The single rank is comprised of eighteen 256Mx4 DDR2 Samsung DRAMs. One IDT (Rev L4) Low Power Advanced Memory Buffer (AMB) is used as the interface between the system memory bus and DIMM DRAMs. One 2K-bit EEPROM is used for Serial Presence Detect. For improved thermal performance, a Full DIMM Heat Spreader with thermal interface material (TIM) is attached to the front and back of the DIMM.

Pin Configurations

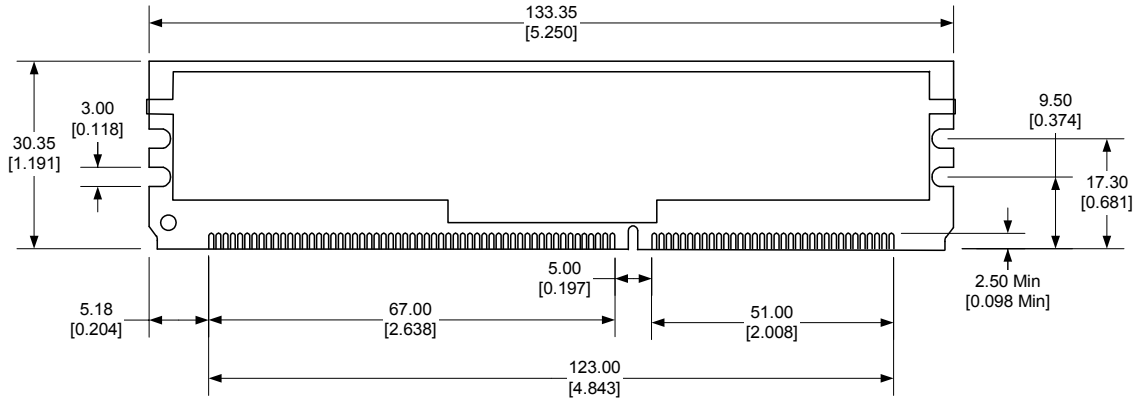
Front side								Back side			
1	VDD	31	PN3	61	/PN9	91	/PS9	121	VDD	151	SN3	181	/SN9	211	/SS9
2	VDD	32	/PN3	62	VSS	92	VSS	122	VDD	152	/SN3	182	VSS	212	VSS
3	VDD	33	VSS	63	PN10	93	PS5	123	VDD	153	VSS	183	SN10	213	SS5
4	VSS	34	PN4	64	/PN10	94	/PS5	124	VSS	154	SN4	184	/SN10	214	/SS5
5	VDD	35	/PN4	65	VSS	95	VSS	125	VDD	155	/SN4	185	VSS	215	VSS
6	VDD	36	VSS	66	PN11	96	PS6	126	VDD	156	VSS	186	/SN11	216	SS6
7	VDD	37	PN5	67	/PN11	97	/PS6	127	VDD	157	SN5	187	/SN11	217	/SS6
8	VSS	38	/PN5	68	VSS	98	VSS	128	VSS	158	/SN5	188	VSS	218	VSS
9	VCC	39	VSS	69	VSS	99	PS7	129	VCC	159	VSS	189	VSS	219	SS7
10	VCC	40	PN13	70	PS0	100	/PS7	130	VCC	160	SN13	190	SS0	220	/SS7
11	VSS	41	/PN13	71	/PS0	101	VSS	131	VSS	161	/SN13	191	/SS0	221	VSS
12	VCC	42	VSS	72	VSS	102	PS8	132	VCC	162	VSS	192	VSS	222	SS8
13	VCC	43	VSS	73	PS1	103	/PS8	133	VCC	163	VSS	193	SS1	223	/SS8
14	VSS	44	RFU	74	/PS1	104	VSS	134	VSS	164	RFU1	194	/SS1	224	VSS
15	VTT	45	RFU	75	VSS	105	RFU2	135	VTT	165	RFU1	195	VSS	225	RFU2
16	VID1	46	VSS	76	PS2	106	RFU2	136	VID0	166	VSS	196	SS2	226	RFU2
17	/RESET	47	VSS	77	/PS2	107	VSS	137	M_TEST	167	VSS	197	/SS2	227	VSS
18	VSS	48	PN12	78	VSS	108	VDD	138	VSS	168	SN12	198	VSS	228	SCK
19	RFU2	49	/PN12	79	PS3	109	VDD	139	RFU2	169	/SN12	199	SS3	229	/SCK
20	RFU2	50	VSS	80	/PS3	110	VSS	140	RFU2	170	VSS	200	/SS3	230	VSS
21	VSS	51	PN6	81	VSS	111	VDD	141	VSS	171	SN6	201	VSS	231	VDD
22	PN0	52	/PN6	82	PS4	112	VDD	142	SN0	172	/SN6	202	SS4	232	VDD
23	/PN0	53	VSS	83	/PS4	113	VDD	143	/SN0	173	VSS	203	/SS4	233	VDD
24	VSS	54	PN7	84	VSS	114	VSS	144	VSS	174	SN7	204	VSS	234	VSS
25	PN1	55	/PN7	85	VSS	115	VDD	145	SN1	175	/SN7	205	VSS	235	VDD
26	/PN1	56	VSS	86	RFU1	116	VDD	146	/SN1	176	VSS	206	RFU1	236	VDD
27	VSS	57	PN8	87	RFU1	117	VTT	147	VSS	177	SN8	207	RFU1	237	VTT
28	PN2	58	/PN8	88	VSS	118	SA2	148	SN2	178	/SN8	208	VSS	238	VDDSPD
29	/PN2	59	VSS	89	VSS	119	SDA	149	/SN2	179	VSS	209	VSS	239	SA0
30	VSS	60	PN9	90	PS9	120	SCL	150	VSS	180	SN9	210	SS9	240	SA1

NOTE: M_TEST is not used

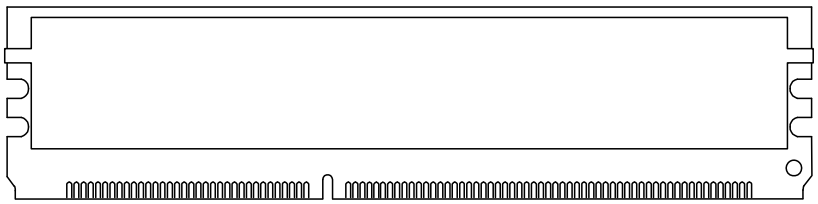
Pin Names

Pin Names	Function
SCK, /SCK	System Clock Input
PN, /PN[13:0]	Primary Northbound Data
PS, /PS[9:0]	Primary Southbound Data
SN. /SN[13:0]	Secondary Northbound Data
SS. /SS[9:0]	Secondary Southbound Data
SCL	Serial Clock, EEPROM
SDA	Serial Data, EEPROM
VID[1:0]	Voltage ID
/RESET	AMB Reset Signal
VCC	AMB Core Power and AMB Channel Interface Power (1.5 V)
VDD	DRAM Power and AMB DRAM I/O Power (1.8 V)
VTT	DRAM Address/Command/Clock Termination Power (VDD/2)
VDDSPD	SPD Power
VSS	Ground
RFU	Reserved For Future Use
DNU	Do Not Use
M_TEST	Margin Test
SA[2:0]	Serial Address, EEPROM

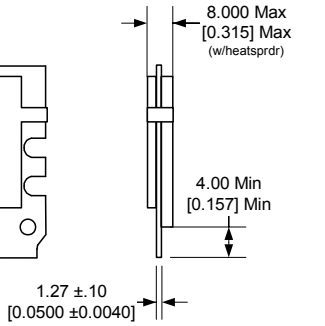
Front view



Back view



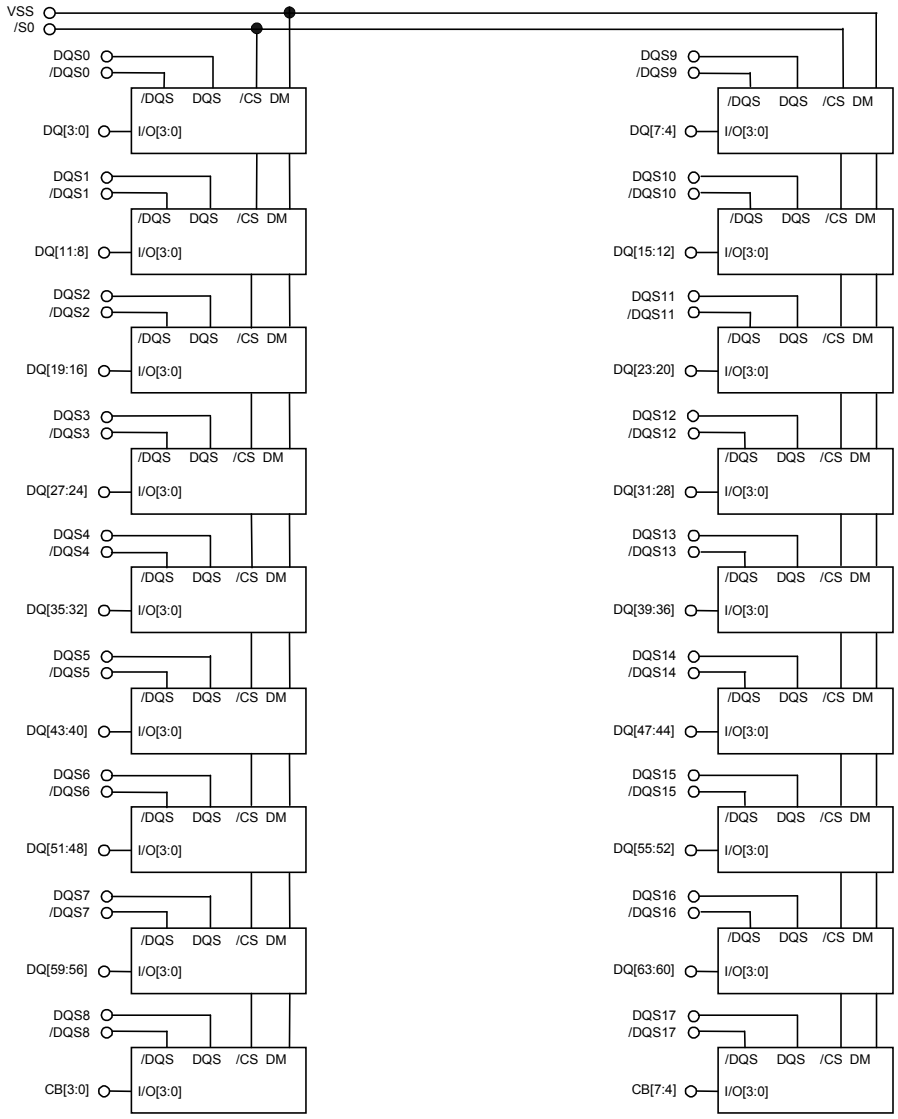
Side view

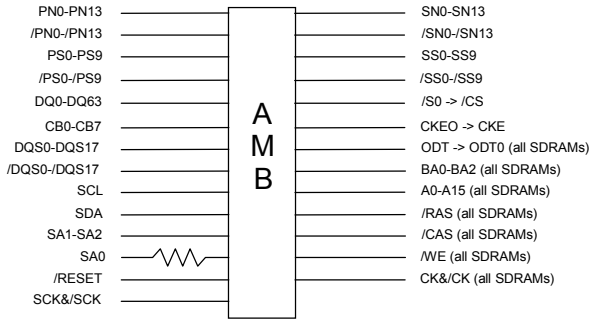


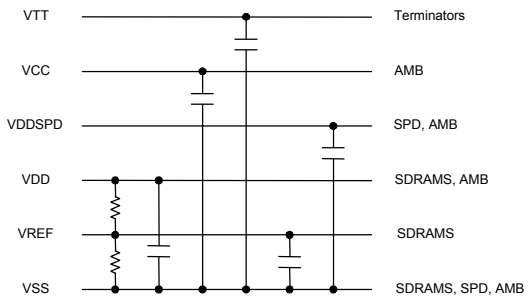
Notes

Tolerances on all dimensions except where otherwise indicated are ±.13 [.005].

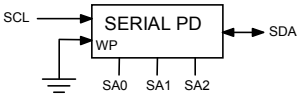
All dimensions are expressed: millimeters [inches]







All address/command/control/clock — V_{TT}



Notes:
1. DQ-to-I/O wiring may be changed within a nibble
2. There are two physical copies of each address/command/control
3. There are four physical copies of each clock

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit	Note
Temperature, DDR2 DRAM Case	T_{Case}	0 to +95	C	1, 2
Temperature, Storage	T_{STG}	-55 to +100	C	1
Operating humidity (relative)	H_{OPR}	10 to 90	%	1
Storage humidity (without condensation)	H_{STG}	5 to 95	%	1
Voltage on any pin relative to V_{SS}	V_{IN},V_{OUT}	-0.3 to 1.75	V	1
Voltage on V_{CC} relative to V_{SS}	V_{CC}	-0.3 to 1.75	V	1
Voltage on V_{DD} relative to V_{SS}	V_{DD}	-0.5 to 2.3	V	1
Voltage on V_{TT} relative to V_{SS}	V_{TT}	-0.5 to 2.3	V	1
Power Dissipation	P_D	21	W	1

NOTES:

1. Exposure to absolute maximum rating conditions for extended period may affect reliability.
2. For 85 C < T_{Case} ≤ 95 C, t_{REFI} = 3.9 µs max.

DC Operating Conditions (T_A = 0 to 70 C, Voltage referenced to V_{SS} = 0V)

Parameter	Symbol	Minimum	Typical	Maximum	Unit	Note
AMB Supply Voltage	V_{CC}	1.425	1.5	1.59	V	
DDR2 Supply Voltage	V_{DD}	1.7	1.8	1.9	V	
Termination Voltage	V_{TT}	0.48 x V_{DD}	0.50 x V_{DD}	0.52 x V_{DD}	V	
EEPROM Supply Voltage (SPD)	V_{DDSPD}	3.0	3.3	3.6	V	
Input High Voltage (SPD)	$V_{IH(DC)}$	2.1		V_{DDSPD}	V	1
Input Low Voltage (SPD)	$V_{IL(DC)}$	1.0			V	1
Input High Voltage (RESET/BFUNC)	$V_{IH(DC)}$	1.0			V	2
Input Low Voltage(RESET/BFUNC)	$V_{IL(DC)}$			0.5	V	2
Leakage Curent (RESET/BFUNC)	I_L	-90		90	µA	2
Leakage Curent (Link)	I_L	-5		5	µA	

Notes:

1. Applies to SMB and SPD bus signals.
2. Applies to AMB CMOS signal /RESET.

Differential Transmitter Output Specification

Parameter	Symbol	MIN	MAX	Units
Differential peak-to-peak output voltage for large voltage swing VTX-DIFFp-p =2 * | VTX-D+ - VTX-D- |	VTX-DIFFp-p_L(1)	900	1300	mV
Differential peak-to-peak output voltage for regular voltage swing VTX-DIFFp-p =2 * | VTX-D+ - VTX-D- |	VTX-DIFFp-p_R(1)	800	---	mV
Differential peak-to-peak output voltage for small voltage swing VTX-DIFFp-p =2 * | VTX-D+ - VTX-D- |	VTX-DIFFp-p_S(1)	520	---	mV
DC common code output voltage for large voltage swing Defined as: VTX-CM = DC(avg) of | VTX-D+ + VTX-D- |/2	VTX-CM_L(1)	---	375	mV
DC common mode output voltage for small voltage swing Defined as: VTX-CM = DC(avg) of | VTX-D+ + VTX-D- |/2	VTX-CM_S(1)	135	280	mV
De-emphasized differential output voltage ratio for -3.5 dB de-emphasis -	VTX-DE-3.5-Ratio(1,2,3)	-3	-4	dB
De-emphasized differential output voltage ratio for -6 dB de-emphasis	VTX-DE-6-Ratio(1,2,3)	-5	-7	dB
AC peak-to-peak common mode output voltage for large swing VTX-CM-AC = Max | VTX-D+ + VTX-D- |/2 - Min | VTX-D+ + VTX-D- |/2	VTX-CM-ACp-p L(1,4)	---	90	mV
AC peak-to-peak common mode output voltage for regular swing VTX-CM-AC = Max | VTX-D+ + VTX-D- |/2 - Min | VTX-D+ + VTX-D- |/2	VTX-CM-ACp-p R(1,4)	---	80	mV
AC peak-to-peak common mode output voltage for small swing VTX-CM-AC = Max | VTX-D+ + VTX-D- |/2 - Min | VTX-D+ + VTX-D- |/2	VTX-CM-ACp-p S(1,4)	---	70	mV
Maximum single-ended voltage in EI condition, DC + AC	VTX-IDLE-SE(5,6)	---	50	mV
Maximum single-ended voltage in EI condition, DC only	VTX-IDLE-SE-DC(5,6,7)	---	20	mV
Maximum peak-to-peak differential voltage in EI condition	VTX-IDLE-DIFFp-p(6)	---	40	mV
Single-ended voltage(w.r.t. VSS) on D+/D-	VTX-SE(1,7)	-75	750	mV
Minimum TX eye width, 3.2 and 4 Gb/s	TTX-Eye-MIN(1,9,10)	0.7	---	UI
Maximum TX deterministic jitter, 3.2 and 4 Gb/s	TTX-DJ-DD(1,9,10,11)	---	0.2	UI
Instantaneous pulse width	TTX-PULSE(12)	0.85	---	UI
Differential TX output rise/fall time Given by 20%-80% voltage levels	TTX-RISE, TTX-FALL(1)	30	90	ps
Mismatch between rise and fall times	TTX-RF-MISMATCH	---	20	ps
Differential return loss Measured over 0.1 GHz to 2.4GHz	RLTX-DIFF	8	---	dB
Common mode return loss Measured over 0.1 GHz to 2.4GHz	RLTX-CM	6	---	dB
Transmitter termination resistance	RTX(13)	41	55	Ω
D+/D- TX resistance difference RTX-Match-DC = 2*| RTX-D+ - RTX-D- |/(RTX-D+ + RTX-D-) Bounds are applied separately to high and low output voltage states	RTX-Match-DC		4	%
Lane-to-lane skew at TX	LTX-SKEW 1(14,16)	---	100+3UI	ps
Lane-to-lane skew at TX	LTX-SKEW 2(15,16)	---	100+2UI	ps
Maximum TX Drift (resync mode)	TTX-DRIFT-RESYNC(17)	---	240	ps
Maximum TX Drift (resample mode only)	TTX-DRIFT-RESAMPLE(17)	---	120	ps
Bit Error Ratio	BER(18)	---	10^{-12}	

NOTES FOR TRANSMITTER OUTPUT SPECIFICATIONS:
1. Specified at the package pins into a timing and voltage compliance test load. Common-mode measurements to be performed using a 101010 pattern.
2. This is the ratio of the $V_{TX-DIFFp-p}$ of the second and following bits after a transition divided by the $V_{TX-DIFFp-p}$ of the first bit after a transition.
3. De-emphasis is disabled in the calibration state.
4. Includes all sources of AC common mode noise
5. Single-ended voltages below that value that are simultaneously detected on D+ and D- are interpreted as the Electrical Idle condition.
6. Specified at the package pins into a voltage compliance test load. Transmitters must meet both single-ended and differential output E1 specifications.
7. This specification, considered with $V_{RX-IDLE-SE-DC}$, implies a maximum 15mV single-ended DC offset between Tx and Rx pins during the electrical idle condition. This in turn allows a ground offset between adjacent FB-DIMM agents of 26mV when worst-case termination resistance matching is considered.
8. The maximum value is specified to be at least ($V_{TX-DIFFp-p}$ L / 4) + V_{TX-CM} L + ($V_{TX-CM-ACp-p}$ / 2)
9. This number does not include the effects of SSC or reference clock jitter.
10. These timing specifications apply to resync mode only.
11. Defined as the dual-dirac deterministic jitter as described in Section 4 of the JEDEC FB-DIMM High Speed Differential PTP Link Draft Spec rev 0.8.
12. Pulse width measured at 0V differential.
13. The termination small signal resistance; tolerance across voltages from 100mV to 400mV shall not exceed ±5: with regard to the average of the values measured at 100mV
and at 400mV for that pin.
14. Lane to Lane skew at the Transmitter pins for an end component.
15. Lane to Lane skew at the Transmitter pins for an intermediate component (assuming zero Lane to Lane skew at the Receiver pins of the incoming PORT).
16. This is a static skew. A FB-DIMM component is not allowed to change its lane to lane phase relationship after initialization.
17. Measured from the reference clock edge to the center of the output eye. This specification is met across specified voltage and temperature ranges for a single component. Drift
rate of change is significantly below the tracking capability of the receiver.
18. BER per differential lane. For a complete definition of Bit Error Ratio, refer to JEDEC's Compliance Methodology section.

Differential Receiver Input Specification

Parameter	Symbol	MIN	MAX	Units
Differential peak-to-peak input voltage VRX-DIFFp-p =2 * | VRX-D+ - VRX-D- |	VRX-DIFFp-p_L(1)	170	1300	mV
Maximum single-ended voltage for EI condition, DC + AC	VRX-IDLE-SE(2,3,4)	---	65	mV
Maximum single-ended voltage for EI condition, DC only	VRX-IDLE-SE-DC(2,3,4,5)	---	35	mV
Single-ended voltage (w.r.t. VSS) on D+/D-	VRX-SE(4)	-300	900	mV
Single-pulse peak differential input voltage	VRX-DIFF-PULSE(4,6)	85	---	mV
Amplitude ratio between adjacent symbols 1100mV < VRX-DIFFp-p ≦1300mV	VRX-DIFF-ADJ-RATIO-HI(4,7)	---	3	
Amplitude ratio between adjacent symbols VRX-DIFFp-p ≦1100mV	VRX-DIFF-ADJ-RATIO(4,7)	---	4	
Maximum RX inherent timing error, 3.2 and 4 Gb/s	TRX-TJ-MAX(4,8,9)	---	0.4	UI
Maximum RX inherent deterministic timing error, 3.2 and 4 Gb/s	TRX-DJ-DD(4,8,9,10)	---	0.3	UI
Single-pulse width at zero-voltage crossing	TRX-PW-ZC(4,6)	0.55	---	UI
Single-pulse width at minimum-level crossing	TRX-PW-ML(4,6)	0.2	---	UI
Differential RX input rise/fall time, given by 20%-80% voltage levels	TRX-RISE,TRX-FALL	50	---	ps
Common mode of the input voltage Defined as: VRX-CM = DC(avg) of | VRX-D+ + VRX-D- |/2	VRX-CM(1,11)	120	400	mV
AC peak-to-peak common mode of input voltage VRX-CM-AC = Max | VRX-D+ + VRX-D- |/2 - Min | VRX-D+ + VRX-D- |/2	VRX-CM-ACp-p(1)	---	270	mV
Ratio of VRX-CM-ACp-p to minimum VRX-DIFFp-p	VRX-CM-EH-Ratio(12)	---	45	%
Differential return loss Measured over 0.1 GHz to 2.4GHz	RLRX-DIFF	9	---	dB
Common mode return loss Measured over 0.1 GHz to 2.4GHz	RLRX-CM	6	---	dB
RX termination resistance	RRX(13)	41	55	Ω
D+/D- RX resistance difference RRX-Match-DC = 2*| RRX-D+ - RRX-D- |/(RRX-D+ + RRX-D-)	RRX-Match-DC	---	4	%
Lane-to-lane PCB skew at RX **Lane to Lane PCB skew at the Receiver that must be tolerated.**	LRX-PCB-SKEW(14)	---	6	UI
Minimum RX Drift Tolerance	TRX-DRIFT(15)	400	---	ps
Minimum data tracking 3dB bandwidth	FTRK(16)	0.2	---	MHz
Electrical idle entry detect time	TEI-ENTRY - DETECT(17)	---	60	ns
Electrical idle exit detect time	TEI-EXIT-DETECT	---	30	ns
Bit Error Ratio	BER(18)	---	10^{-12}	

NOTES FOR RECEIVER INPUT SPECIFICATIONS:
1. Specified at the package pins into a timing and voltage compliant test setup. Note that signal levels at the pad are lower than at the pin.
2. Single-ended voltages below that value that are simultaneously detected on D+ and D- are interpreted as the Electrical Idle condition. Worst-case margins are determined by comparing EI levels with common mode levels during normal operation for the case with transmitter using small voltage swing (see RX Single-ended Electrical Idle Levels and RX Common Mode Levels).
3. Multiple lanes need to detect the EI condition before the device can act upon the EI detection.
4. Specified at the package pins into a timing and voltage compliance test setup.
5. This specification, considered with $V_{TX\text{-}IDLE\text{-}SE\text{-}DC}$, implies a maximum 15mV single-ended DC offset between TX and RX pins during the elecrical idle condition. This in turn allows a ground offset between adjacent FB-DIMM of 26mV when worstcase termination resistance matching is considered.
6. The single-pulse mask provides sufficient symbol energy for reliable RX reception. Each symbol complies with both the single-pulse mask and the cumulative eye mask (see RX Single-Pulse Min Width and Amplitude Mask, Pulse Shifted Early, and RX Single-Pulse Min Width and Amplitude Mask, Pulse Shifted Late).
7. The relative amplitude ratio limit between adjacent symbols prevents excessive inter-symbol interference in the Rx. Each symbol must comply with the peak amplitude ratio with regard to both the preceding and subsequent symbols (see RX Maximum Adjacent Symbol Amplitude).
8. This number does not include the effects of SSC or reference clock jitter.
9. This number includes setup and hold of the RX sampling flop.
10. Defined as the dual-dirac deterministic timing error as described in Section 4.2.2 of the JEDEC FB-DIMM High-Speed Differential PTP Link Draft Spec, rev 0.8.
11. Allows for 15mV DC offset between transmit and receive devices. 12. The received differential signal satisfies both this ratio as well as the absolute maximum AC peak-to-peak common mode specification. For example, if $V_{RX\text{-}DIFFp\text{-}p}$ is 200mV, the maximum AC peak-to-peak common mode is the lesser of (200 mV * 0.45 = 90mV) and $V_{RX\text{-}CM\text{-}ACp\text{-}p}$.
13. The termination small signal resistance; tolerance across voltages from 100mV to 400mV shall not exceed ±5∧ with regard to the average of the values measured at 100mV and at 400mV for that pin.
14. This number represents the lane-to-lane skew between TX and RX pins and does not include the transmitter output skew from the component driving the signal to the receiver. This is one component of the end-to-end channel skew in the AMB specification.
15. Measured from the reference clock edge to the center of the input eye. This specification is met across specified voltage and temperature ranges. Drift rate of change is significantly below the tracking capability of the receiver.
16. This bandwidth number assumes the specified minimum data transition density. Maximum jitter at 0.2MHz is 0.05UI.
17. The specified time includes the time required to forward the EI entry condition.
18. BER per differential lane.

Advanced Memory Buffer FBD Timing/Electrical

Parameter	Symbol	MIN	MAX	Units
EI Assertion Pass-Through Timing	tEI PROPAGATE		4	CLKs
EI Deassertion Pass-Through Timing	tEID		tBitlock	CLKs
EI Assertion Duration	tEI	100		CLKs
Bit Lock Interval	tBITLOCK		119	Frames
Frame Lock Interval	tFRAMELOCK		154	Frames

Advanced Memory Buffer Latency Parameters

Parameter	Symbol	MIN	MAX	Units	Notes
CMD2DATA = 0x40 (Data Rate = 667)	tC2D_AMB	16.2	19	ns	
CMD2DATA = 0x46 (Data Rate = 667)	tC2D_AMB	17.7	20.5	ns	
Resample Delay (6)	tRESAMPLE	0.9	1.4	ns	1
Resync Delay (7,8,9)	tRESYNC	2	3.2	ns	2

NOTES:
1. tRESAMPLE is the delay from the southbound input to the southbound output, or the northbound input to the northbound output when in resample mode, measured from the center of the data eye.
2. tRESYNC is the delay from the southbound input to the southbound output, or the northbound input to the northbound output when in resync mode, measured from the center of the data eye.

AMB Power Specification (T_A = 0 to 70 C, Voltage referenced to V_{SS} = 0V)

Parameter	Symbol	Test Condition	Power Supply	Value	Unit
Idle Current	IDD_IDLE_0	Single or last FBDIMM: L0 state, idle (0 BW); primary channel enabled, secondary channel disabled, CKE high; command and address lines stable, DDR2 SDRAM clock active.	1.5 V	2300	mA
			1.8 V	550	
Idle Current	IDD_IDLE_1	First FBDIMM**:** L0 state, idle (0 BW); primary and secondary channels enabled, CKE high; command and address lines stable, DDR2 SDRAM clock active.	1.5 V	3000	mA
			1.8 V	550	
Active Power	IDD_TDP_0	TDP BW, Single or Last DIMM; L0 State; TDP Channel BW=2.4GB/s@667, 67% READ, 33% WRITE; primary channel enabled; secondary channel disabled, CKE high; command and address lines stable, DDR2 SDRAM clock active.	1.5 V	2700	mA
			1.8 V	1000	
Active Power	IDD_TDP_1	TDP BW, First DIMM; L0 State; TDP Channel BW=2.4GB/s@667, DIMM BW=1.6GB/s@667; 67% READ, 33% WRITE; primary channel enabled; secondary channel enabled, CKE high; command and address lines stable, DDR2 SDRAM clock active.	1.5 V	3600	mA
			1.8 V	750	
Training	IDD_TRAINING	Primary and secondary channels enabled; 100% toggle on all channel lanes; DDR2 SDRAM devices idle (0 BW); CKE HIGH, command and address lines stable; DDR2 SDRAM clock active.	1.5 V	3700	mA
			1.8 V	0.5	

DRAM AC Characteristics (AC operating conditions unless otherwise noted)

Parameter	Symbol	Min Value	Max Value	Unit	Note
Row Cycle Time	t_{RC}	60	-	ns	
Auto Refresh Row Cycle Time	t_{RFC}	127.5	-	ns	
Row Active Time	t_{RAS}	45	70K	ns	
Row Address to Column Address Delay	t_{RCD}	15	-	ns	
Row Active to row Active Delay	t_{RRD}	7.5	-	ns	
Column Address to Column Address Delay	t_{CCD}	2	-	CLK	
Row Precharge time	t_{RP}	15	-	ns	
Write Recovery Time	t_{WR}	15	-	ns	
Auto Precharge Write Recovery + Precharge Time	t_{DAL}	$(t_{WR}/ t_{CK}) + (t_{RP}/ t_{CK})$	-	ns	
System Clock Cycle Time	t_{CK}	3000	8000	ps	
Clock High Level Width	t_{CH}	0.45	0.52	CLK	
Clock Low Level Width	t_{CL}	0.45	0.52	CLK	
DQ output access time from CK & /CK	t_{AC}	-0.450	+0.450	ns	
DQS-Out edge to Clock Edge skew	t_{DQSCK}	-0.400	+0.400	ns	
DQS-Out edge to Data-out edge skew	t_{DQSQ}	-	0.240	ns	
Data-Out hold time from DQS	t_{QH}	$t_{HP} - t_{QHS}$	-	ns	1
Data hold skew factor	t_{QHS}	-	0.340	ns	1
Clock Half Period	t_{HP}	min (t_{CL} , t_{CH})	-	ns	1
Input Setup Time (fast slew rate)	t_{IS}	0.200	-	ns	2,3,5,6
Input Hold Time (fast slew rate)	t_{IH}	0.275	-	ns	2,3,5,6
Input Pulse Width	t_{IPW}	0.6	-	CLK	6
Write DQS High Level Width	t_{DQSH}	0.35	-	CLK	
Write DQS Low Level Width	t_{DQSL}	0.35	-	CLK	
CLK to First Rising edge to DQS-In	t_{DQSS}	-0.25	+0.25	CLK	
Data-In Setup Time to DQS-In (DQ & DM)	t_{DS}	0.100	-	ns	7
Data-In Hold Time to DQS-In (DQ & DM)	t_{DH}	0.175	-	ns	7

NOTES:
1. This calculation accounts for t_{DQSQ}(max), the pulse width distortion of on-chip and jitter.
2. Data sampled at the rising edges of the clock: A0~A13, BA0~BA1, CKE, /S0, /RAS, /CAS, /WE
3. For command/address input slew rate > = 1.0 V/ns
4. For command/address input slew rate > = 0.5 V/ns and <1.0 V/ns
5. CK,/CK slew rates are > = 1.0V/ns
6. These Parameters guarantee device timing, but they are not necessarily tested on each device, and they may be guaranteed by design or tester correlation.
7. Data latched at both rising and falling edges of Data Strobes (DQS)

AC Operating Conditions (AC operating conditions unless otherwise noted)

Parameter	Symbol	Min Value	Max Value	Unit	Note
DQ Input Pulse Width	t_{DIPW}	0.35	-	CLK	
Read DQS Preamble Time	t_{RPRE}	0.9	1.1	CLK	
Read DQS Postamble Time	t_{RPST}	0.4	0.6	CLK	
Write DQS Preamble Setup Time	t_{WPRES}	0	-	ns	
Write DQS Preamble Hold Time	t_{WPRE}	0.35	-	CLK	
Write DQS Postamble Time	t_{WPST}	0.4	0.6	CLK	
Mode Register Set Delay	t_{MRD}	2	-	CLK	
Exit Self Refresh to Non-Read Command	t_{XSNR}	tRFC + 10	-	ns	
Exit Self Refresh to Read Command	t_{XSRD}	200	-	CLK	
Average Periodic Refresh Interval	t_{REFI}	-	7.8	µs	1
		-	3.9	µs	2

NOTES:
1. For 0 C < T_{Case} ≤ 85 C
2. For 85 C < T_{Case} ≤ 95 C

SERIAL PRESENCE DETECT MATRIX

Byte#	Function.	Value	Hex
0	Number of Serial PD Bytes Written / SPD Device Size / CRC Coverage		0x92
	Bit 3 ~ Bit 0. SPD Bytes Used -	176	
	Bit 6 ~ Bit 4. SPD Bytes Total -	256	
	Bit 7. CRC Coverage -	Bytes 0-116	
1	SPD Revision	Rev. 1.1	0x11
2	Key Byte / DRAM Device Type	DDR2 FBDIMM	0x09
3	Voltage Levels of this Assembly		0x12
	Bit 3 ~ Bit 0. Power Supply 1 -	1.5V	
	Bit 7 ~ Bit 4. Power Supply 2 -	1.8V	
4	SDRAM Addressing		0x49
	Bit 1, 0. Number of Banks -	8	
	Bit 5 ~ Bit 3.Column Address Bits -	11	
	Bit 7 ~ Bit 5. Row Address Bits -	14	
5	Module Physical Attributes		0x23
	Bit 3 ~ Bit 0. Module Thickness (mm) -	7<x<=8.0	
	Bit 4 ~ Bit 2. Module Height (mm) -	30<x<=35	
	Bit 7, 6. Reserved	0	
6	Module Type		0x07
	Bit 3 ~ Bit 0. Module Type -	FB-DIMM	
	Bit 7 ~ Bit 4. Reserved	0	
7	Module Organization		0x08
	Bit 3 ~ Bit 0. SDRAM Device Width -	4-Bits	
	Bit 5 ~ Bit 3. Number of Ranks -	1-Rank	
	Bit 7, 6. Reserved	0	
8	Fine Timebase Dividend / Divisor		0x00
	Bit 3 ~ Bit 0. Fine Timebase (FTB) Dividend -	0	
	Bit 7 ~ Bit 4. Fine Timebase (FTB) Divisor -	0	
9	Medium Timebase Dividend.	1 (MTB = 0.25ns)	0x01
10	Medium Timebase Divisor.	4 (MTB = 0.25ns)	0x04
11	SDRAM Minimum Cycle Time (tCKmin).	3.0ns	0x0C
12	SDRAM Maximum Cycle Time (tCKmax).	8.0ns	0x20
13	SDRAM CAS Latencies Supported.		0x24
	Bit 3 ~ Bit 0. Minimum CL (clocks) -	4	
	Bit 7 ~ Bit 4. CL Range (clocks) -	2	
14	SDRAM Minimum CAS Latency Time (tAAmin).	15.0ns	0x3C
15	SDRAM Write Recovery Times Supported		0x42
	Bit 3 ~ Bit 0. Minimum WR (clocks) -	2	
	Bit 7 ~ Bit 4. WR Range (clocks) -	4	
16	SDRAM Write Recovery Time (tWR).	15.0ns	0x3C
17	SDRAM Write Latencies Supported		0x42
	Bit 3 ~ Bit 0. Minimum WL (clocks) -	2	

	Bit 7 ~ Bit 4. WL Range (clocks) -	4	
18	SDRAM Additive Latencies Supported.		0x40
	Bit 3 ~ Bit 0. Minimum AL (clocks)-	0	
	Bit 7 ~ Bit 4. AL Range (clocks) -	4	
19	SDRAM Minimum RAS to CAS Delay (tRCD).	15.0ns	0x3C
20	SDRAM Minimum Row Active to Row Active Delay (tRRD).	7.5ns	0x1E
21	SDRAM Minimum Row Precharge Time (tRP).	15.0ns	0x3C
22	SDRAM Upper Nibbles for tRAS and tRC.		0x00
	Bit 3 ~ Bit 0. tRAS Most Significant Nibble -		
	Bit 7 ~ Bit 4. tRC Most Significant Nibble -		
23	SDRAM Minimum Active to Precharge Time (tRAS).	45.0ns	0xB4
24	SDRAM Minimum Active to Active/Refresh Time (tRC).	60.0ns	0xF0
25	SDRAM Minimum Refresh Recovery Time Delay (tRFC), (LSB).	127.5ns	0xFE
26	SDRAM Minimum Refresh Recovery Time Delay (tRFC), (MSB).	127.5ns	0x01
27	SDRAM Minimum Internal Write to Read Command Delay (tWTR).	7.5ns	0x1E
28	SDRAM Minimum Internal Read to Precharge Command Delay (tRTP).	7.5ns	0x1E
29	SDRAM Burst Lengths Supported		0x03
	Bit 0. BL = 4 -	X	
	Bit 1. BL = 8 -	X	
	Bit 6 ~ Bit 2.TBD		
	Bit 7. Burst Chop -		
30	SDRAM Terminations Supported.		0x07
	Bit 0. 150 ohms ODT -	X	
	Bit 1. 75 ohms ODT -	X	
	Bit 2. 50 ohms ODT -	X	
	Bit 6 ~ Bit 3.TBD		
31	SDRAM Drivers Supported.		0x01
	Bit 0. Weak Driver -	X	
	Bit 7 ~ Bit 1. TBD		
32	SDRAM Average Refresh Interval (tREFI) / Double Refresh mode bit / High Temperature self-refresh rate support indication.		0xC2
	Bit 0 ~ Bit 3. Average Refresh Interval (tREFI) uS -	7.8	
	Bit 5, Bit 4. TBD	0	
	Bit 6. High Temperature Self-Refresh -	1-Required	
	Bit 7. Double Refresh Requirement -	1-Supported	
33	Tcasemax Delta.		0x53
	Bit 3 ~ Bit 0. DT4R4W Delta, Subfield B: 0.4 °C -	1.2	
	Bit 7 ~ Bit 4. Tcasemax, Subfield A: 2 °C -	10	
34	Thermal Resistance of SDRAM Package. °C/W	69	0x8A
35	SDRAM Case Temperature Rise from Ambient due to Activate-Precharge minus 2.8 °C offset temperature (DT0). °C		0x78
	Bit 1, Bit 0. Reserved	0	
	Bit 7 ~ Bit 2. DT0 -	9	
36	SDRAM Case Temperature Rise from Ambient due to Precharge/Quiet	5.9	0x3B

	Standby (DT2N/DT2Q). °C		
37	SDRAM Case Temperature Rise from Ambient due to Precharge Power-Down (DT2P). °C	1.05	0x46
38	SDRAM Case Temperature Rise from Ambient due to Active Standby (DT3N). °C	7.8	0x34
39	SDRAM Case Temperature Rise from Ambient due to Page Open Burst Read/DT4R4W Mode Bit (DT4R/DT4R4W Mode Bit).		0x76
	Bit 0. DT4R4W Mode Bit, Subfield B: 0.4 °C	0	
	Bit 7 ~ Bit 1. DT4R, Subfield A: 0.4 °C -	23.6	
40	SDRAM Case Temperature Rise from Ambient due to Burst Refresh (DT5B). °C	23.5	0x2F
41	SDRAM Case Temperature Rise from Ambient due to Bank Interleave Reads with Auto-Precharge (DT7). °C	29	0x3A
42-74	Reserved	UNUSED	0x00
75	QR Control.		0x00
76	QR ODT control for Rank 0 and rank 1 Reads and writes.		0x00
77	QR ODT1 and ODT2 control for reads.		0x00
78	FBD ODT Definition for Rank 2 and 3		0x00
	Bit 1, Bit 0. Rank 2 Data DRAM ODT -	Disabled	
	Bit 3, Bit 2. Rank 2 Ecc DRAM ODT -	Disabled	
	Bit 5, Bit 4. Rank 3 Data DRAM ODT -	Disabled	
	Bit 7, Bit 6. Rank 3 Ecc DRAM ODT -	Disabled	
79	FBD ODT Definition for Rank 0 and 1		0x02
	Bit 1, Bit 0. Rank 0 Data DRAM ODT -	150 Ohms	
	Bit 3, Bit 2. Rank 0 Ecc DRAM ODT -	Disabled	
	Bit 5, Bit 4. Rank 1 Data DRAM ODT -	Disabled	
	Bit 7, Bit 6. Rank 1 Ecc DRAM ODT -	Disabled	
80	Reserved	UNUSED	0x00
81	Channel Protocols Supported, Least Significant Byte		0x02
	Bit 0, DDR2 Base Non-ECC Protocol -	0-Not Supported	
	Bit 1. DDR2 Base ECC Protocol -	1-Supported	
	Bit 7 ~ Bit 2. TBD	0	
82	Channel Protocols Supported, Most Significant Byte	UNUSED	0x00
83	Back-to-back Turnaround Cycles		0x10
	Bit 1, Bit 0. Rank Read-to-Read -	0 add-l clock	
	Bit 3, Bit 2. Write-to-Read -	0 add-l clock	
	Bit 5, Bit 4. Read-to-Write -	1 add-l clock	
	Bit 7, Bit 6. TBD	0	
84	AMB Read Access Time for DDR2-800 (AMB.LINKPARNXT[1:0] = 11)		0x36
	Bit 3 ~ Bit 0. Read Access Fine Granularity (UI)	6	
	Bit 7 ~ Bit 4. Read Access Coarse Granularity (tCK)	3	
85	AMB Read Access Time for DDR2-667 (AMB.LINKPARNXT[1:0] = 10)		0x34
	Bit 3 ~ Bit 0. Read Access Fine Granularity (UI)	4	
	Bit 7 ~ Bit 4. Read Access Coarse Granularity (tCK)	3	
86	AMB Read Access Time for DDR2-533 (AMB.LINKPARNXT[1:0] = 01)		0x32
	Bit 3 ~ Bit 0. Read Access Fine Granularity (UI)	2	
	Bit 7 ~ Bit 4. Read Access Coarse Granularity (tCK)	3	

87	Thermal Resistance of AMB Package from Top (Case) to Ambient (Psi T-A AMB). °C/W	21	0x2A
88	AMB Case Temperature Rise from Ambient due to AMB in Idle_0 State (DT AMB Idle_0). °C	86	0x56
89	AMB Case Temperature Rise from Ambient due to AMB in Idle_1 State (DT AMB Idle_1). °C	107	0x6B
90	AMB Case Temperature Rise from Ambient due to AMB in Idle_2 State (DT AMB Idle_2). °C	92	0x5C
91	AMB Case Temperature Rise from Ambient due to AMB in Active_1 State (DT AMB Active_1). °C	145	0x91
92	AMB Case Temperature Rise from Ambient due to AMB in Active_2 State (DT AMB Active_2). °C	118	0x76
93	AMB Case Temperature Rise from Ambient due to AMB in L0s State (DT AMB L0s). °C	UNUSED	0x00
94-97	Reserved	UNUSED	0x00
98	AMB Junction Temperature Maximum (Tjmax). °C	125	0x1F
99	Reserved		0x0A
100	Reserved	UNUSED	0x00
101	AMB Personality Bytes: Pre-initialization.		0x00
102	AMB Personality Bytes: Pre-initialization.		0xE2
103	AMB Personality Bytes: Pre-initialization.		0x62
104	AMB Personality Bytes: Pre-initialization.		0x20
105	AMB Personality Bytes: Pre-initialization.		0x80
106	AMB Personality Bytes: Pre-initialization.		0x9C
107,108	AMB Personality Bytes: Post-initialization.		0x00
109	AMB Personality Bytes: Post-initialization.		0xF0
110	AMB Personality Bytes: Post-initialization.		0x70
111-114	AMB Personality Bytes: Post-initialization.		0x60
115	AMB Manufacturer's JEDEC ID Code.		0x7F
116	AMB Manufacturer's JEDEC ID Code.		0xB3
117	Module ID: Module Manufacturer's JEDEC ID Code.		0x01
118	Module ID: Module Manufacturer's JEDEC ID Code.		0x91
119	Module ID: Module Manufacturing Location.		0x01
120,121	Module ID: Module Manufacturing Location.		0x00
122-125	Module ID: Module Serial Number.		0x00
126	Cyclical Redundancy Code (CRC).		0x21
127	Cyclical Redundancy Code (CRC).		0xE9
128-131	Module Part Number		0x20
132	Module Part Number	D	0x44
133	Module Part Number	A	0x41
134	Module Part Number	T	0x54

135	Module Part Number	A	0x41
136	Module Part Number	R	0x52
137	Module Part Number	A	0x41
138	Module Part Number	M	0x4D
139	Module Part Number		0x20
140	Module Part Number	6	0x36
141	Module Part Number	5	0x35
142	Module Part Number	5	0x35
143	Module Part Number	2	0x32
144	Module Part Number	7	0x37
145	Module Part Number		0x20
146,147	Module Revision Code	UNUSED	0x00
148,149	SDRAM Manufacturer's JEDEC ID Code	UNUSED	0x00
150	Manufacturer's Specific Data		0x01
151	Manufacturer's Specific Data		0x09
152-175	Manufacturer's Specific Data	UNUSED	0x00
176-255	Open for customer use	UNUSED	0x00

DATARAM CORPORATION, USA Corporate Headquarters, P.O. Box 7528, Princeton, NJ 08543-7528;
Voice: 609-799-0071, Fax: 609-799-6734; www.dataram.com

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